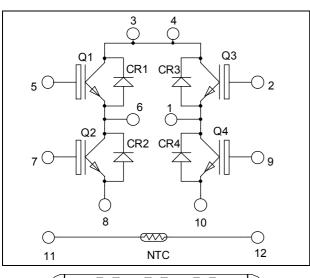
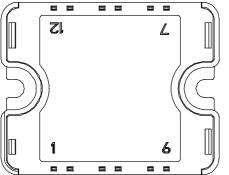


# Full - Bridge Trench + Field Stop IGBT3

Power Module





Pins 3/4 must be shorted together

## $V_{CES} = 600V$ $I_{C} = 75A^{*}$ @ Tc = 80°C

**APTGT75H60T1G** 

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	100*	
1 <sub>C</sub>	I <sub>C</sub> Continuous Collector Current T	$T_C = 80^{\circ}C$	75*	А
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	150A @ 550V	

\* Specification of IGBT device but output current must be limited to 40A to not exceed a delta of temperature greater than 35°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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#### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified • • • •

Electrical Characteristics									
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit			
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA			
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_j = 25^{\circ}C$		1.5	1.9	V			
V CE(sat)	Concetor Emitter Saturation Voltage	$I_{\rm C} = 75 {\rm A}$ $T_{\rm j} = 150^{\circ} {\rm C}$	2	1.7		v			
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600 \mu A$	5.0	5.8	6.5	V			
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA			

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit		
Cies	Input Capacitance	$V_{GE} = 0V$			4620			
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 25V$			300		pF	
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		140				
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			110			
Tr	Rise Time	$V_{GE} = \pm 15V$			45		ns	
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 75A$			200			
T <sub>f</sub>	Fall Time	$R_G = 4.7\Omega$		40				
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch $V_{GE} = \pm 15V$	ning (150°C)		120			
Tr	Rise Time	$V_{GE} = \pm 15 V$ $V_{Bus} = 300 V$			50		ns	
T <sub>d(off)</sub>	Turn-off Delay Time	$I_{C} = 75A$ $R_{G} = 4.7\Omega$				250		
T <sub>f</sub>	Fall Time				60			
Б	Turn on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.35		mJ	
Eon	Turn-on Switching Energy	$V_{Bus} = 300V$	$T_{j} = 150^{\circ}C$		0.6		111J	
Б	Turn-off Switching Energy	$I_{\rm C} = 75 \text{A}$	$T_j = 25^{\circ}C$		2.2		mJ	
E <sub>off</sub>	run-on Switching Energy	$R_G = 4.7\Omega \qquad T_j = 150^{\circ}C$		2.6		111J		

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	$V_{R}=600V$	$T_j = 25^{\circ}C$			250	μA
IRM	Maximum Reverse Leakage Current	VR 000V	$T_{j} = 150^{\circ}C$			500	μΑ
I <sub>F</sub>	DC Forward current		$Tc = 80^{\circ}C$		75		А
V <sub>F</sub>	Diode Forward Voltage	$I_{\rm F} = 75 A$ $V_{\rm GE} = 0 V$	$T_i = 25^{\circ}C$		1.6	2	
• F	blode i of ward voltage		$T_i = 150^{\circ}C$		1.5		V
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۹r	Reverse receivery Time		$T_{j} = 150^{\circ}C$		150		115
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$		3.6		
Qrr	Reverse Recovery Charge			$T_{j} = 150^{\circ}C$		7.6	
Er	Reverse Recovery Energy		$T_i = 25^{\circ}C$		0.85		mJ
Ľr	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		1.8		1113

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## APTGT75H60T1G

## Thermal and package characteristics

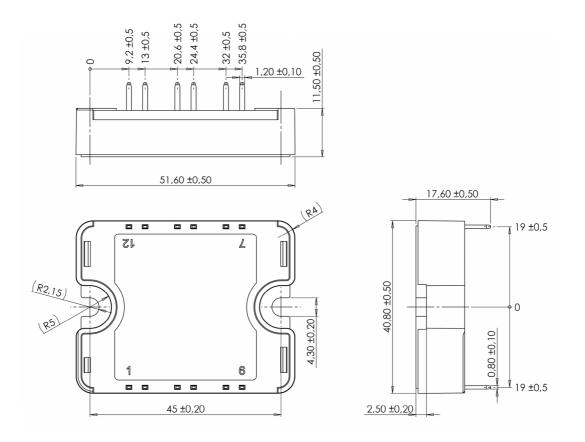
Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT			0.60	°C/W	
<b>R</b> <sub>thJC</sub>		Diode			0.98	C/ W	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		175	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature		-40		100		
Torque	Mounting torque	To heatsink	x M4	2		3	N.m
Wt	Package Weight					80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

## SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

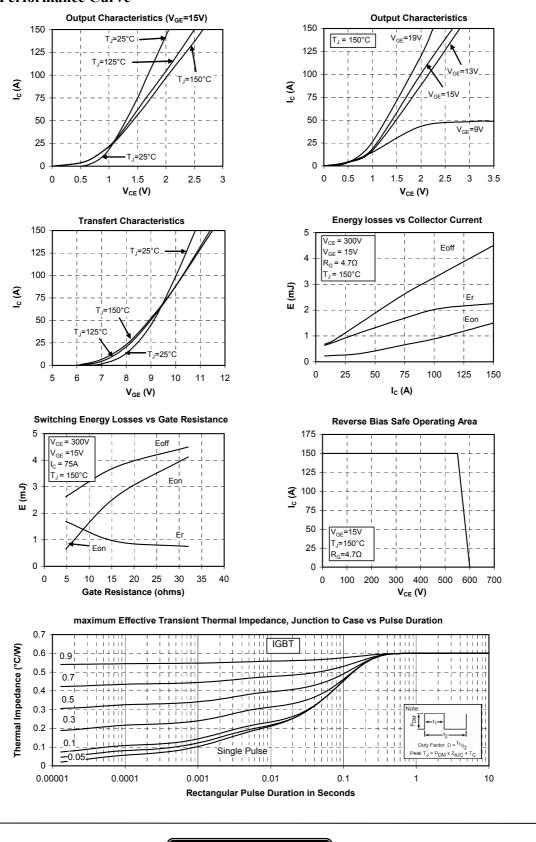
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### **Typical Performance Curve**

## **APTGT75H60T1G**



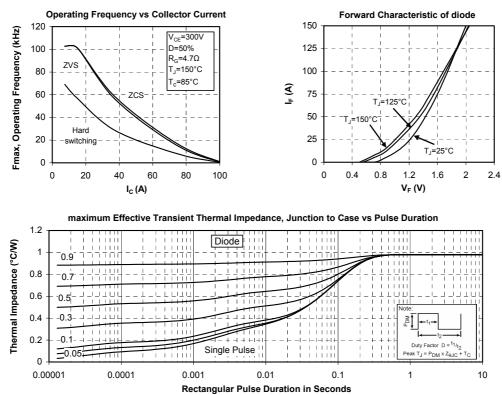
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## APTGT75H60T1G

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